

Tool ID: 120
Tool Location: 103

Equipment Information Sheet

LPCVD CMOS Nitride - E4

Manager: Phil Infante 607-254-4926
Backup: Aaron Windsor 607-254-4831

Calls to staff phones will be automatically forwarded to their cell phones during accessible hours. At other times leave a message or send them an email.

SAFETY

- The furnaces are run at elevated temperatures of 400-1200°C and use flammable, toxic, and corrosive gases.

USAGE RESTRICTIONS

- No changing of gas flows or process parameters without staff approval
- Max temperature of 800 C

SCHEDULING/SIGN-UP RESTRICTIONS

Minimum Tool Time: 90 minutes

- Reservation blocks greater than 8 hrs must be cleared by a MOS staff person prior to reserving the time

MATERIALS COMPATIBILITY CATEGORY

| Tool Category 1:Restricted Silicon Based Materials Only | |
|---|--|
| Allowed | Not Allowed |
| Silicon Based Materials only (Si, SiC, SiO ₂ substrates) | No Evaporated, Sputtered, or Spin on Films |
| All Furnace grown or deposited films | No ALD films |
| PECVD Films | No Metal or Organic Films |
| | No Glass Substrates |
| | No III/V Compound Semiconductors |
| | No Deep Silicon Etched Samples (versaline, Unaxis) |
| | No Organic/Biology Molecules prepared-with or without Salt buffers |

Additional Material Restrictions and Exceptions

- MOS CLEAN required prior to use
- Only use MOS designated holders, wands and tweezers

Last Updated: 03/20/2019